

AMPS RX Cellular Base Station Low Noise Amplifier 821 - 851 MHz

AM-216

V2.00

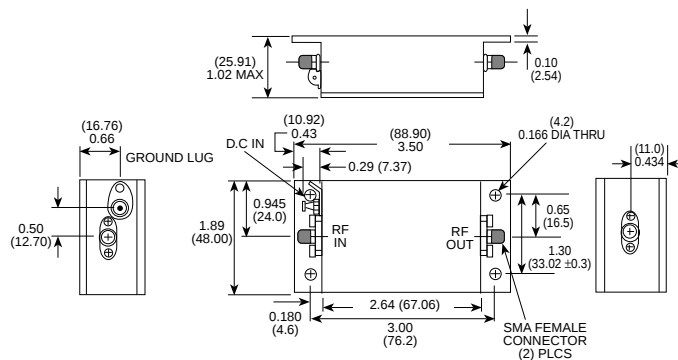
Features

- GaAs FET Technology for Low Noise Figure: 0.8 dB
- Class A Linear Operation for Minimal Distortion
- Low Cost SMT Modular Design Approach
- Reverse Bias Protection and Internal Regulation
- Maximum RF Input Power: +10 dBm
- Rugged Connectorized Housing
- Customized Options Available

Description

The AM-216 is a high performance low noise amplifier in a low cost connectorized housing. The AM-216 is designed for use in AMPS receive band cellular base stations. Utilizing a GaAs FET input stage, the AM-216 is ideally suited for low noise, high gain, high dynamic range and low power consumption applications.

C-40



Dimensions in () are in mm.
Unless Otherwise Noted: .xxx = ± 0.010 (.xx = ± 0.25)
.xx = ± 0.02 (.x = ± 0.5)
WEIGHT (APPROX.): 13.60 OUNCES 3.8 GRAMS

Ordering Information

Part Number	Package
AM-216 SMA	SMA Connectors

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{IN} = +19\text{ V to } +31\text{ VDC}$

Parameter	Units	Min.	Typ.	Max.
Gain	dB	43	44	45
Noise Figure	dB	-	0.8	1.5
Input VSWR	-	-	1.3:1	1.5:1
Output VSWR	-	-	1.7:1	2.0:1
Output IP_3	dBm	34	36	-
Bias Current	mA	-	185	220

Specifications Subject to Change Without Notice.

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Typical Performance Curves @ +25°C

